

# FCPF250N65S3R0L

## MOSFET – Power, N-Channel, SUPERFET III, Easy Drive

650 V, 12 A, 250 mΩ

### Description

SUPERFET III MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provides superior switching performance, and withstand extreme dv/dt rate. Consequently, SUPERFET III MOSFET Easy drive series helps manage EMI issues and allows for easier design implementation.

### Features

- 700 V @  $T_J = 150^\circ\text{C}$
- Typ.  $R_{DS(on)} = 210\text{ m}\Omega$
- Ultra Low Gate Charge (Typ.  $Q_g = 24\text{ nC}$ )
- Low Effective Output Capacitance (Typ.  $C_{oss(eff.)} = 248\text{ pF}$ )
- 100% Avalanche Tested
- These Devices are Pb-Free and are RoHS Compliant

### Applications

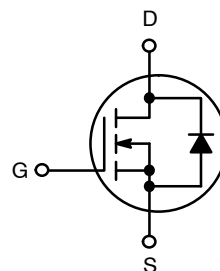
- Computing / Display Power Supplies
- Telecom / Server Power Supplies
- Industrial Power Supplies
- Lighting / Charger / Adapter



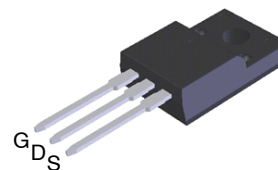
ON Semiconductor®

[www.onsemi.com](http://www.onsemi.com)

$V_{DSS}$	$R_{DS(on)}\text{ MAX}$	$I_D\text{ MAX}$
650 V	250 mΩ @ 10 V	12 A

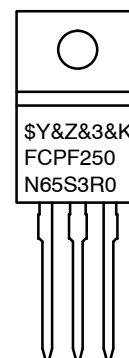


POWER MOSFET



TO-220F  
CASE 340BF

### MARKING DIAGRAM



\$Y = ON Semiconductor Logo  
&Z = Assembly Plant Code  
&3 = Data Code (Year & Week)  
&K = Lot  
FCPF250N65S3R0 = Specific Device Code

### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

# FCPF250N65S3R0L

## ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C, Unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>DSS</sub>	Drain to Source Voltage	650	V
V <sub>GSS</sub>	Gate to Source Voltage	- DC	±30
		- AC (f > 1 Hz)	±30
I <sub>D</sub>	Drain Current	- Continuous (T <sub>C</sub> = 25°C)	12*
		- Continuous (T <sub>C</sub> = 100°C)	7.6*
I <sub>DM</sub>	Drain Current	- Pulsed (Note 1)	30*
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	57	mJ
I <sub>AS</sub>	Avalanche Current (Note 2)	2.3	A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	0.31	mJ
dv/dt	MOSFET dv/dt	100	V/ns
	Peak Diode Recovery dv/dt (Note 3)	20	
P <sub>D</sub>	Power Dissipation	(T <sub>C</sub> = 25°C)	31
		- Derate Above 25°C	0.25
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds	300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

\*Drain current limited by maximum junction temperature.

1. Repetitive rating; pulse-width limited by maximum junction temperature.
2. I<sub>AS</sub> = 2.3 A, R<sub>G</sub> = 25 Ω, starting T<sub>J</sub> = 25°C.
3. I<sub>SD</sub> ≤ 6 A, di/dt ≤ 200 A/μs, V<sub>DD</sub> ≤ 400 V, starting T<sub>J</sub> = 25°C.

## THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R <sub>θJC</sub>	Thermal Resistance, Junction to Case, Max.	4.07	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient, Max.	62.5	

## PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
FCPF250N65S3R0L	FCPF250N65S3R0	TO-220F	Tube	N/A	N/A	50 Units

# FCPF250N65S3R0L

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
--------	-----------	-----------------	------	------	------	------

### OFF CHARACTERISTICS

BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 1 mA, T <sub>J</sub> = 25°C	650			V
		V <sub>GS</sub> = 0 V, I <sub>D</sub> = 1 mA, T <sub>J</sub> = 150°C	700			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 1 mA, Referenced to 25°C		0.67		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 520 V, T <sub>C</sub> = 125°C		0.77		
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0 V			±100	nA

### ON CHARACTERISTICS

V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 0.29 mA	2.5		4.5	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 6 A		210	250	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 20 V, I <sub>D</sub> = 6 A		7.4		S

### DYNAMIC CHARACTERISTICS

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 400 V, V <sub>GS</sub> = 0 V, f = 1 MHz		1010		pF
C <sub>oss</sub>	Output Capacitance			25		pF
C <sub>oss(eff.)</sub>	Effective Output Capacitance	V <sub>DS</sub> = 0 V to 400 V, V <sub>GS</sub> = 0 V		248		pF
C <sub>oss(er.)</sub>	Energy Related Output Capacitance	V <sub>DS</sub> = 0 V to 400 V, V <sub>GS</sub> = 0 V		33		pF
Q <sub>g(tot)</sub>	Total Gate Charge at 10 V	V <sub>DS</sub> = 400 V, I <sub>D</sub> = 6 A, V <sub>GS</sub> = 10 V (Note 4)		24		nC
Q <sub>gs</sub>	Gate to Source Gate Charge			6.1		nC
Q <sub>gd</sub>	Gate to Drain "Miller" Charge			9.7		nC
ESR	Equivalent Series Resistance	f = 1 MHz		1.1		Ω

### SWITCHING CHARACTERISTICS

t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 400 V, I <sub>D</sub> = 6 A, V <sub>GS</sub> = 10 V, R <sub>g</sub> = 4.7 Ω (Note 4)		15		ns
t <sub>r</sub>	Turn-On Rise Time			13		ns
t <sub>d(off)</sub>	Turn-Off Delay Time			40		ns
t <sub>f</sub>	Turn-Off Fall Time			7.2		ns

### SOURCE-DRAIN DIODE CHARACTERISTICS

I <sub>S</sub>	Maximum Continuous Source to Drain Diode Forward Current			12		A
I <sub>SM</sub>	Maximum Pulsed Source to Drain Diode Forward Current			30		A
V <sub>SD</sub>	Source to Drain Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 6 A		1.2		V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>DD</sub> = 400 V, I <sub>SD</sub> = 6 A, dI <sub>F</sub> /dt = 100 A/μs		251		ns
Q <sub>rr</sub>	Reverse Recovery Charge			3.4		μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

TYPICAL PERFORMANCE CHARACTERISTICS

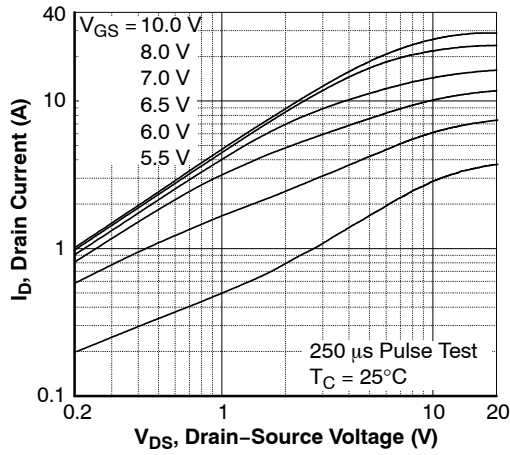


Figure 1. On-Region Characteristics

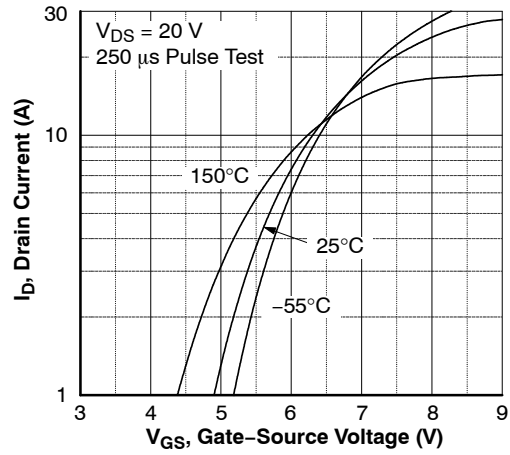


Figure 2. Transfer Characteristics

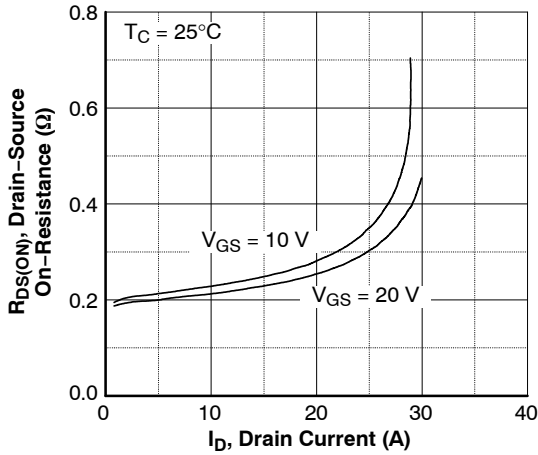


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

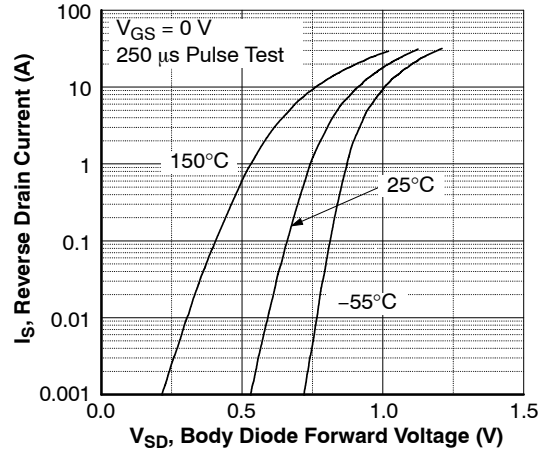


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

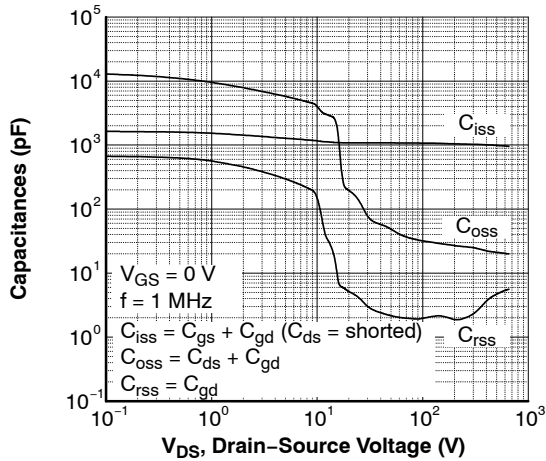


Figure 5. Capacitance Characteristics

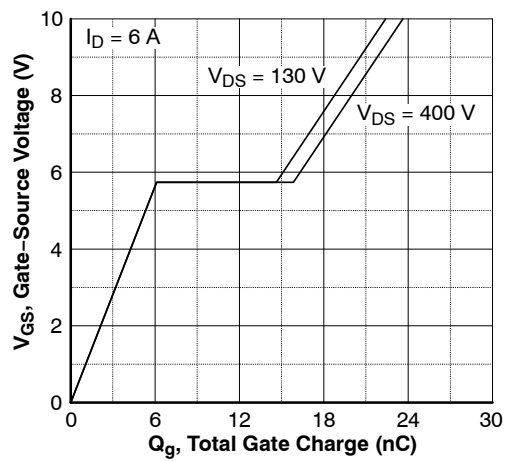


Figure 6. Gate Charge Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

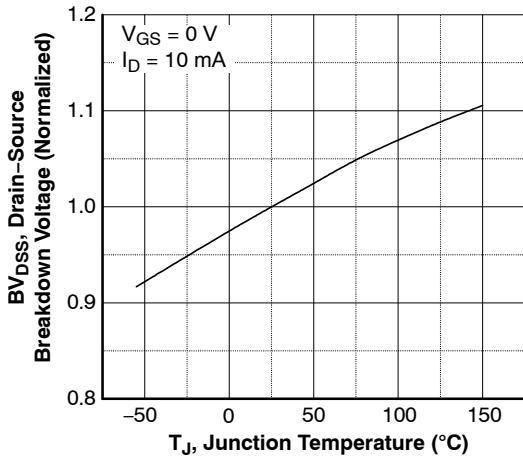


Figure 7. Breakdown Voltage Variation vs. Temperature

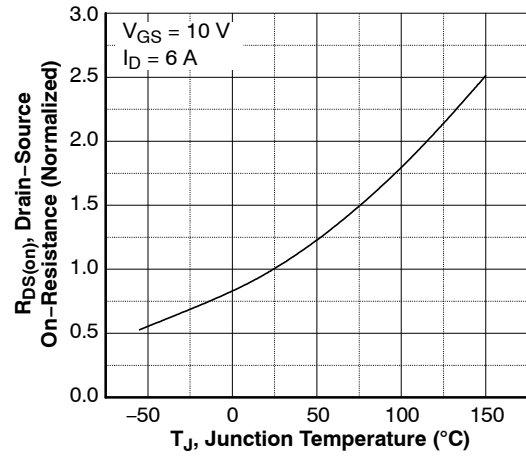


Figure 8. On-Resistance Variation vs. Temperature

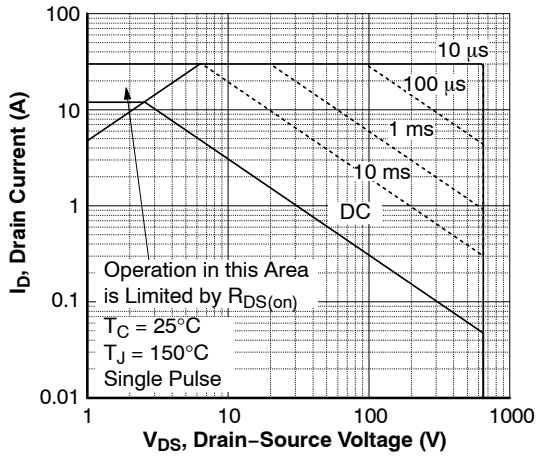


Figure 9. Maximum Safe Operating Area

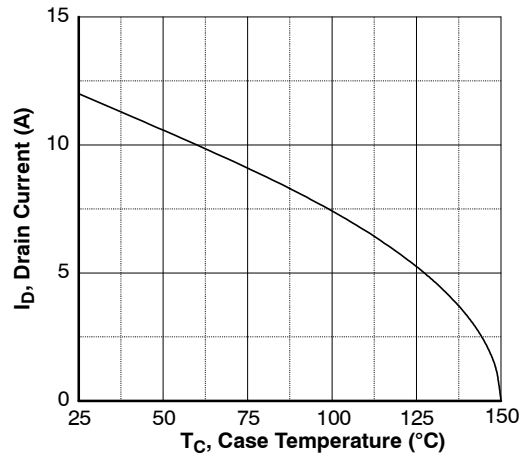


Figure 10. Maximum Drain Current vs. Case Temperature

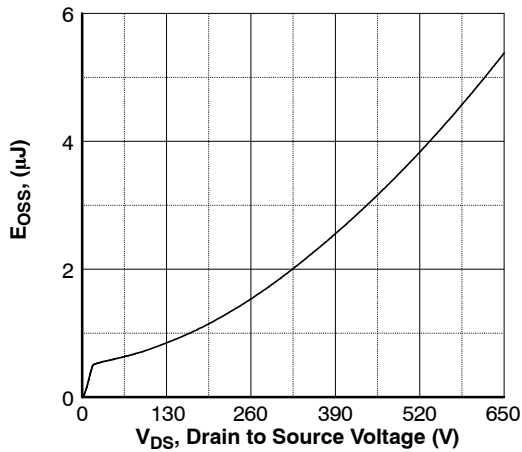


Figure 11.  $E_{OSS}$  vs. Drain to Source Voltage

# FCPF250N65S3R0L

## TYPICAL PERFORMANCE CHARACTERISTICS (continued)

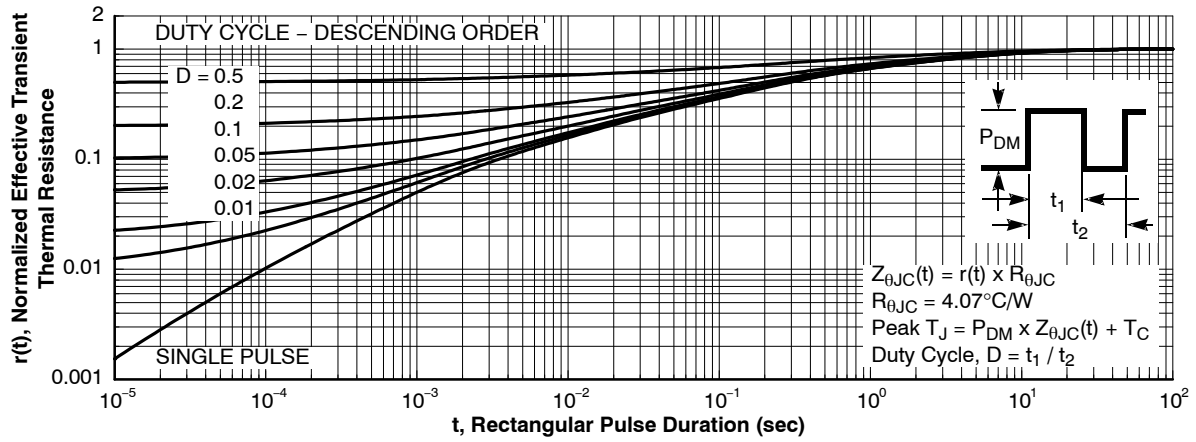


Figure 12. Transient Thermal Response Curve



Figure 13. Gate Charge Test Circuit & Waveform

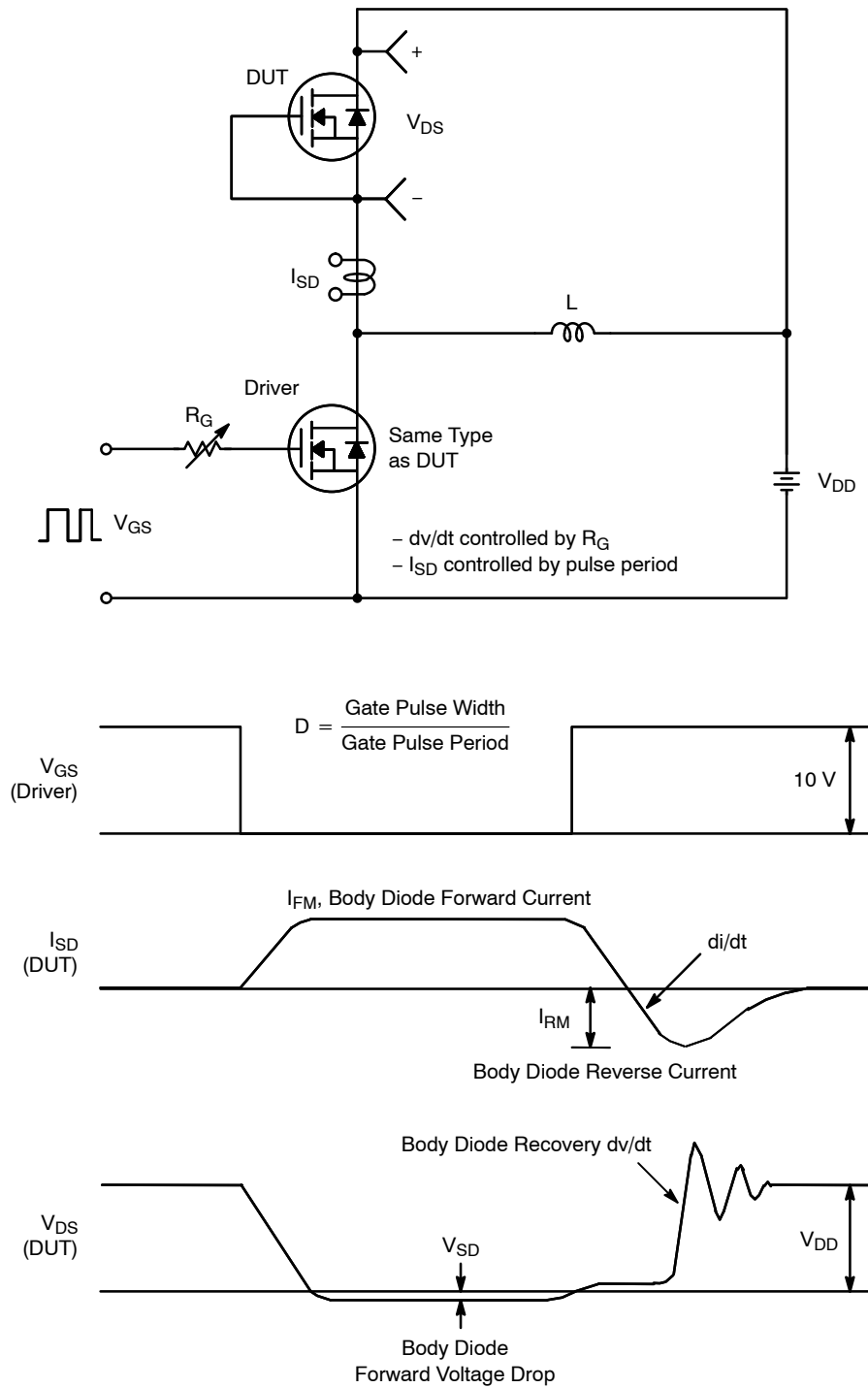


Figure 14. Resistive Switching Test Circuit & Waveforms



Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

# FCPF250N65S3R0L



**Figure 16. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms**



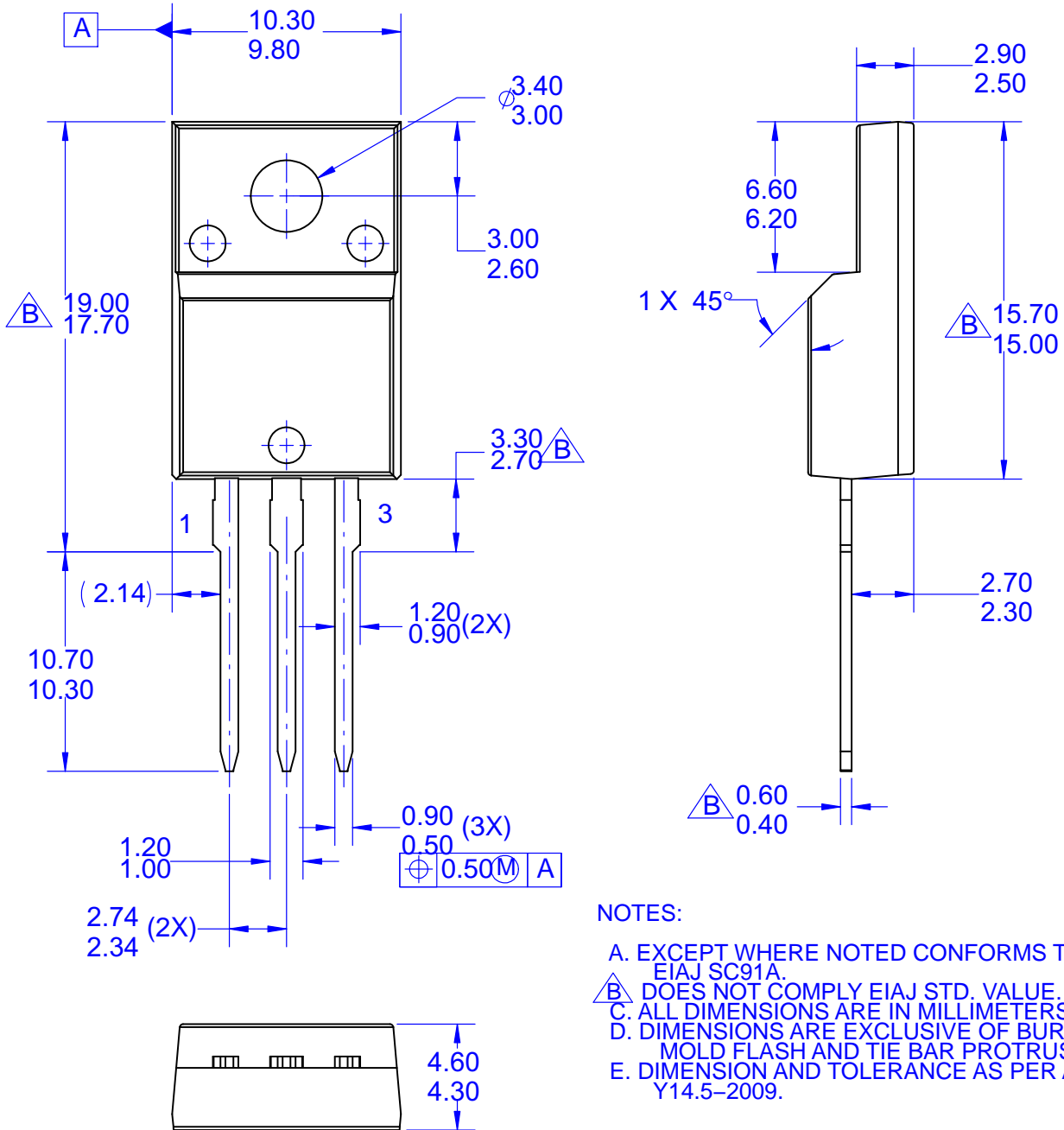
**MECHANICAL CASE OUTLINE**  
**PACKAGE DIMENSIONS**

ON Semiconductor®



**TO-220 FULLPAK 3LD**  
CASE 340BF  
ISSUE O

DATE 31 AUG 2016



**NOTES:**

- A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
- B. DOES NOT COMPLY EIAJ STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.

<b>DOCUMENT NUMBER:</b>	<b>98AON13839G</b>	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
<b>STATUS:</b>	<b>ON SEMICONDUCTOR STANDARD</b>	
<b>NEW STANDARD:</b>		
<b>DESCRIPTION:</b>	<b>TO-220 FULLPAK 3LD</b>	<b>PAGE 1 OF 2</b>



ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor  
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA  
**Phone:** 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
**Fax:** 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
**Email:** [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**N. American Technical Support:** 800-282-9855 Toll Free  
USA/Canada  
**Europe, Middle East and Africa Technical Support:**  
Phone: 421 33 790 2910

**ON Semiconductor Website:** [www.onsemi.com](http://www.onsemi.com)

**Order Literature:** <http://www.onsemi.com/orderlit>

For additional information, please contact your local  
Sales Representative